

P-Channel Power MOSFET

-20V, -6.4A, 40mΩ

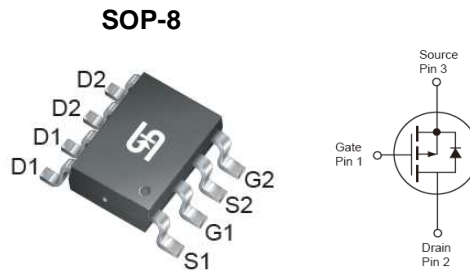
Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

- Load Switch
- PA Switch

KEY PERFORMANCE PARAMETERS		
PARAMETER	VALUE	UNIT
V_{DS}	-20	V
$R_{DS(on)}$ (max)	$V_{GS} = -10V$	40
	$V_{GS} = -4.5V$	60
Q_g	19	nC



Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current ^(Note 1)	I_D	$T_C = 25^\circ C$	-6.4
		$T_C = 100^\circ C$	-3.8
Pulsed Drain Current ^(Note 2)	I_{DM}	-19.2	A
Total Power Dissipation @ $T_A = 25^\circ C$	P_{DTOT}	2.5	W
Single Pulsed Avalanche Energy ^(Note 3)	E_{AS}	13.94	mJ
Single Pulsed Avalanche Current ^(Note 3)	I_{AS}	16.7	A
Operating Junction and Storage Temperature Range	T_J, T_{STG}	- 55 to +150	$^\circ C$

THERMAL PERFORMANCE			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\theta JC}$	30	$^\circ C/W$
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	50	$^\circ C/W$

Notes: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design. $R_{\theta JA}$ shown below for single device operation on FR-4 PCB in still air.

ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu A$	BV_{DSS}	-20	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu A$	$V_{GS(TH)}$	-0.4	--	-1.0	V
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I_{GSS}	--	--	± 100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -16V, V_{GS} = 0V$	I_{DSS}	--	--	-1	μA
On-State Drain Current	$V_{DS} \leq -5V, V_{GS} = -4.5V$	$I_{D(ON)}$	-10	--	--	A
Drain-Source On-State Resistance	$V_{GS} = -4.5V, I_D = -6.4A$	$R_{DS(ON)}$	--	31	40	m Ω
	$V_{GS} = -2.5V, I_D = -5.1A$		--	45	60	
Forward Transconductance	$V_{DS} = -9V, I_D = -6.4A$	g_{fs}	--	14	--	S
Dynamic (Note 5)						
Total Gate Charge	$V_{DS} = -10V, I_D = -6.4A,$ $V_{GS} = -4.5V$	Q_g	--	12	19	nC
Gate-Source Charge		Q_{gs}	--	1.7	--	
Gate-Drain Charge		Q_{gd}	--	3.3	--	
Input Capacitance	$V_{DS} = -10V, V_{GS} = 0V,$ $f = 1.0\text{MHz}$	C_{iss}	--	1020	--	pF
Output Capacitance		C_{oss}	--	191	--	
Reverse Transfer Capacitance		C_{rss}	--	140	--	
Gate Resistance	$F = 1\text{MHz}, \text{open drain}$	R_g	--	3	--	Ω
Switching (Note 6)						
Turn-On Delay Time	$V_{DD} = -10V,$ $R_{GEN} = 6\Omega,$ $I_D = -1A, V_{GS} = -4.5V,$	$t_{d(on)}$	--	25	40	ns
Turn-On Rise Time		t_r	--	43	65	
Turn-Off Delay Time		$t_{d(off)}$	--	71	110	
Turn-Off Fall Time		t_f	--	48	75	
Source-Drain Diode (Note 4)						
Forward On Voltage	$I_S = -2.5A, V_{GS} = 0V$	V_{SD}	--	-0.9	-1.2	V
Reverse Recovery Time	$I_S = -4A$ $dI_F/dt = 100A/\mu s$	t_{rr}	--	12.6	--	ns
Reverse Recovery Charge		Q_{rr}	--	2.84	--	nC

Notes:

1. Current limited by package
2. Pulse width limited by the maximum junction temperature
3. $L = 0.1\text{mH}, I_{AS} = 16.7A, V_{DD} = 25V, R_G = 25\Omega, \text{Starting } T_J = 25^\circ\text{C}$
4. Pulse test: $PW \leq 300\mu s, \text{duty cycle} \leq 2\%$
5. For DESIGN AID ONLY, not subject to production testing.
6. Switching time is essentially independent of operating temperature.

ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM9434CS RLG	SOP-8	2,500pcs / 13" Reel

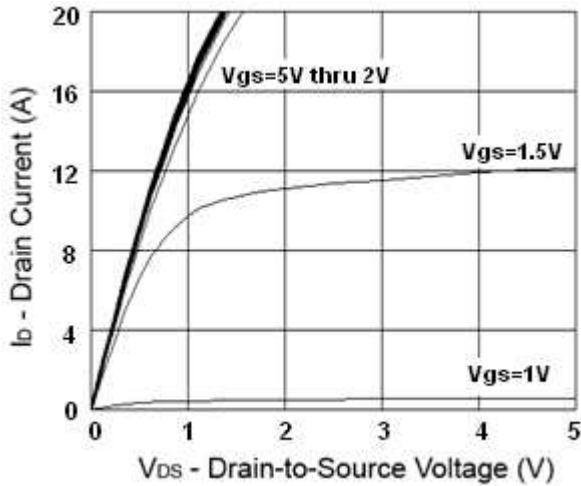
Note:

1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
2. Halogen-free according to IEC 61249-2-21 definition

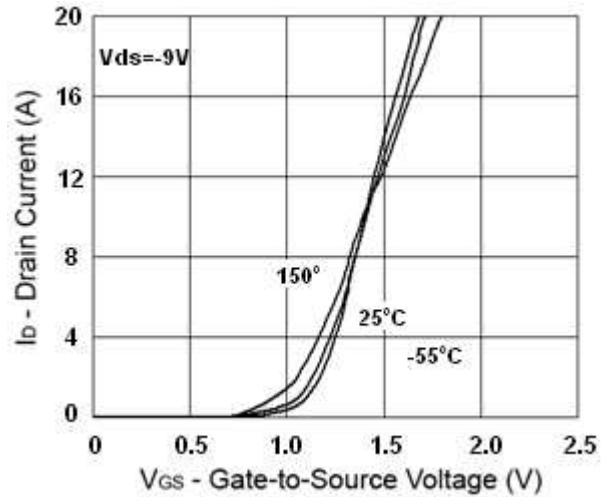
CHARACTERISTICS CURVES

($T_C = 25^\circ\text{C}$ unless otherwise noted)

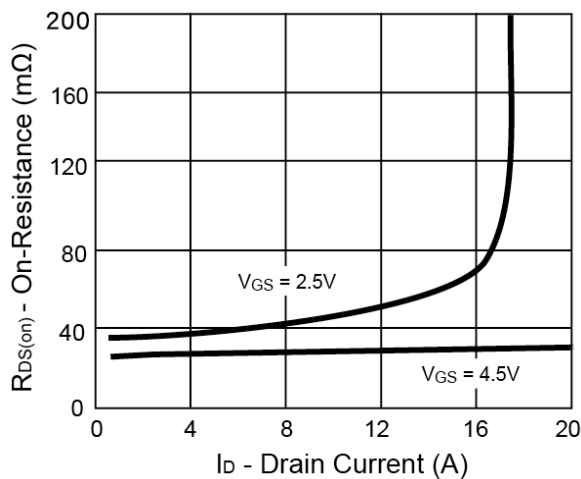
Output Characteristics



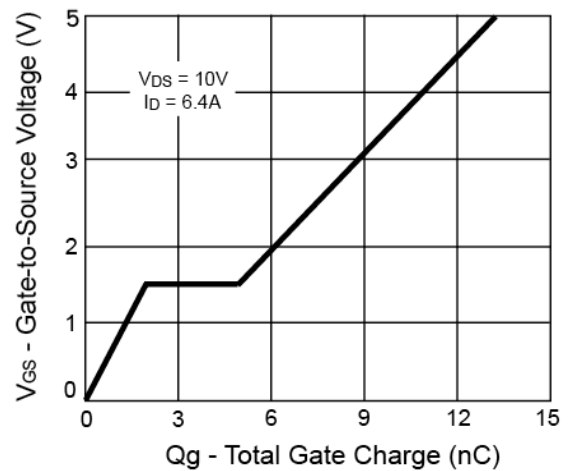
Transfer Characteristics



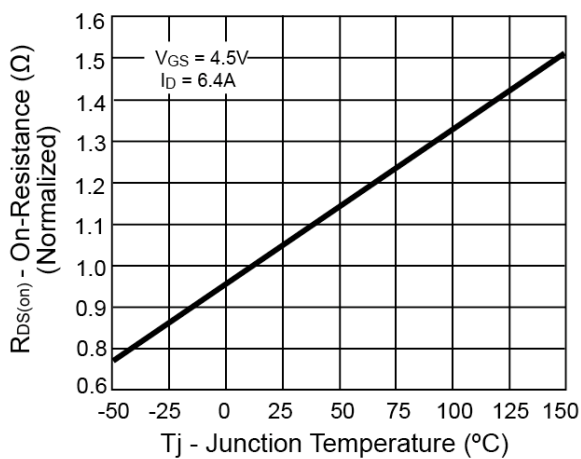
On-Resistance vs. Drain Current



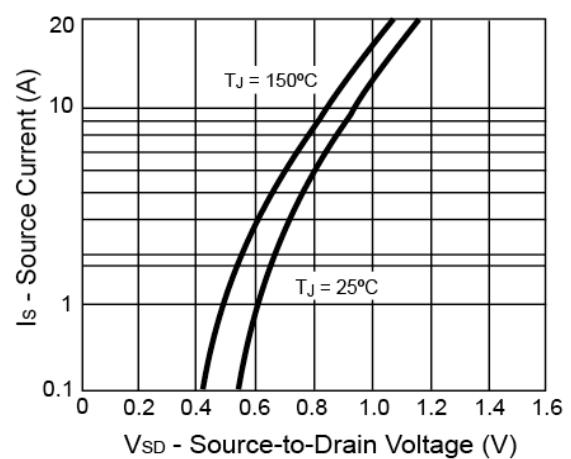
Gate Charge



On-Resistance vs. Junction Temperature



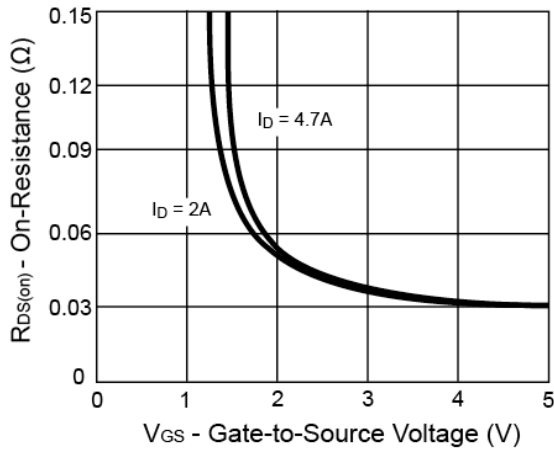
Source-Drain Diode Forward Voltage



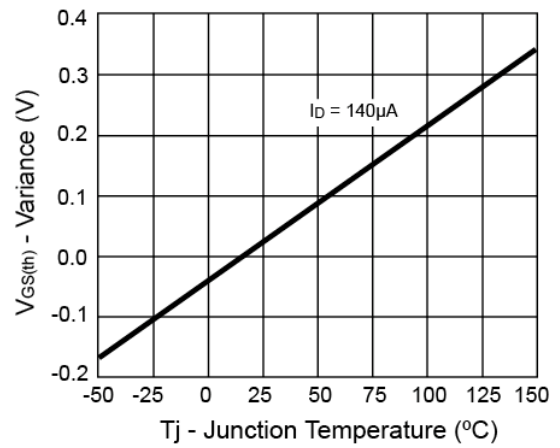
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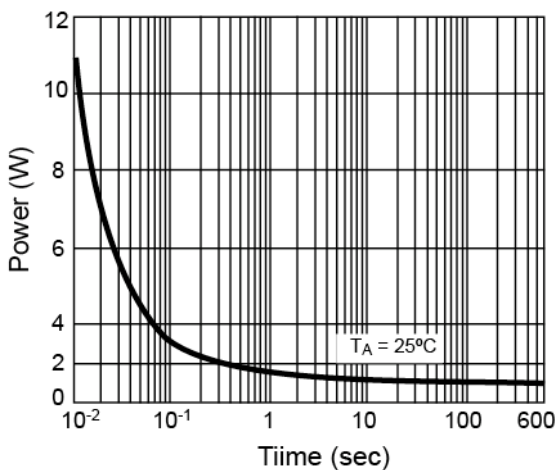
On-Resistance vs. Gate-Source Voltage



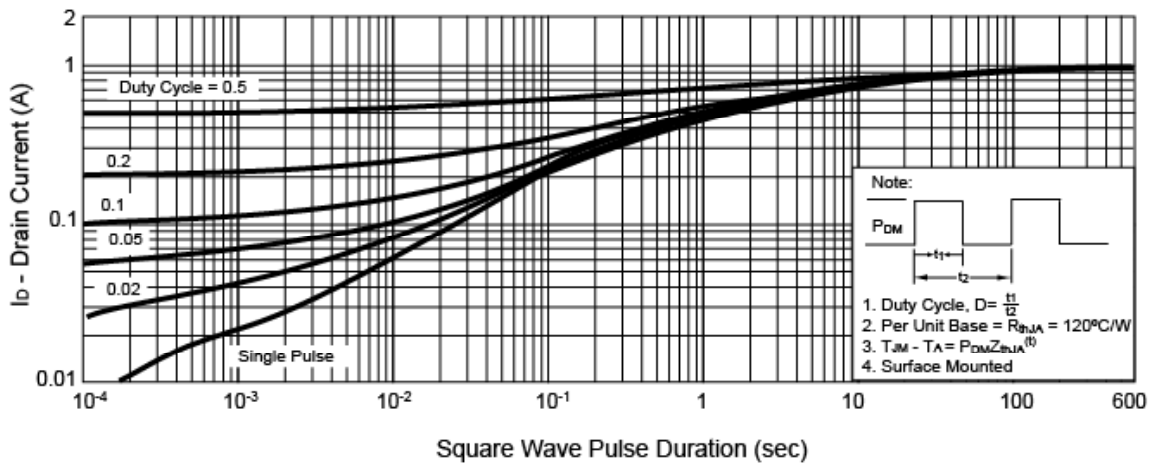
Threshold Voltage



Single Pulse Power

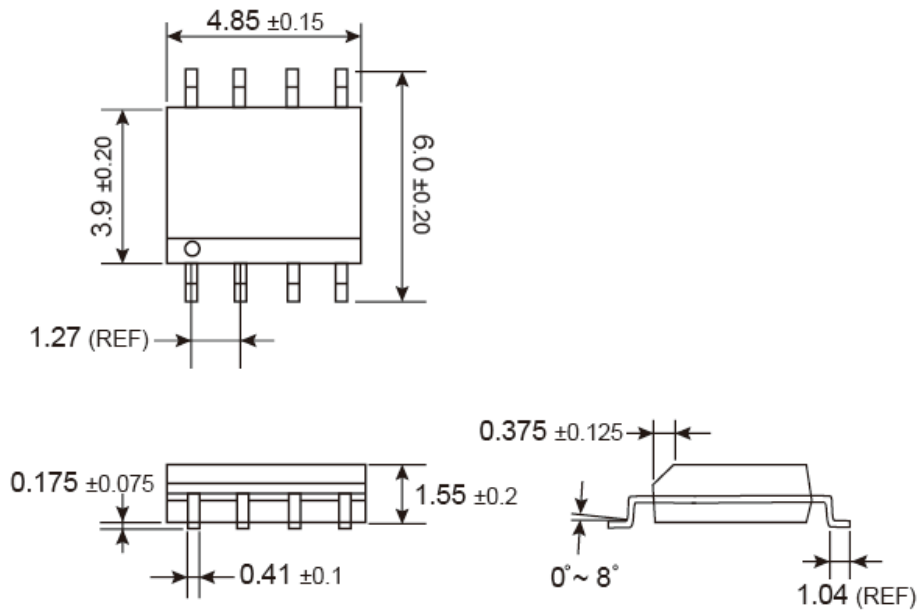


Normalized Thermal Transient Impedance, Junction-to-Ambient

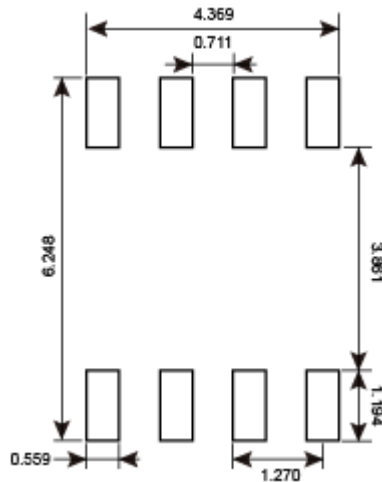


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

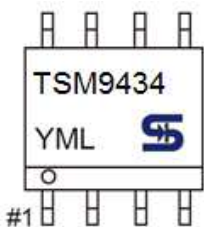
SOP-8



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



- Y = Year Code
- M = Month Code for Halogen Free Product
 - O =Jan P =Feb Q =Mar R =Apr
 - S =May T =Jun U =Jul V =Aug
 - W =Sep X =Oct Y =Nov Z =Dec
- L = Lot Code (1~9, A~Z)

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